TECHNICAL REPORT

ISO/TR 18392

First edition 2005-12-01

Surface chemical analysis — X-ray photoelectron spectroscopy — Procedures for determining backgrounds

Analyse chimique des surfaces — Spectroscopie de photoélectrons X — Protocoles pour déterminer les fonds continus



PDF disclaimer

This PDF file may contain embedded typefaces. In accordance with Adobe's licensing policy, this file may be printed or viewed but shall not be edited unless the typefaces which are embedded are licensed to and installed on the computer performing the editing. In downloading this file, parties accept therein the responsibility of not infringing Adobe's licensing policy. The ISO Central Secretariat accepts no liability in this area.

Adobe is a trademark of Adobe Systems Incorporated.

Details of the software products used to create this PDF file can be found in the General Info relative to the file; the PDF-creation parameters were optimized for printing. Every care has been taken to ensure that the file is suitable for use by ISO member bodies. In the unlikely event that a problem relating to it is found, please inform the Central Secretariat at the address given below

© ISO 2005

All rights reserved. Unless otherwise specified, no part of this publication may be reproduced or utilized in any form or by any means, electronic or mechanical, including photocopying and microfilm, without permission in writing from either ISO at the address below or ISO's member body in the country of the requester.

ISO copyright office Case postale 56 • CH-1211 Geneva 20 Tel. + 41 22 749 01 11 Fax + 41 22 749 09 47 E-mail copyright@iso.org Web www.iso.org

Published in Switzerland

Contents Page Forewordiv Introductionv 1 Scope 1 2 Terms and definitions....... 1 3 Symbols and abbreviated terms 1 Types of background in XPS 1 4 5 Estimation and removal of inelastic electron scattering from electron spectra......2 6 6.1 6.2 6.2.1 6.2.2 6.2.3 6.2.4 Removal based on the electron inelastic-scattering cross-section 4 Procedures accounting for both inelastic and elastic scattering...... 5 6.3 6.4 Less commonly used procedures...... 5 6.5 Role of surface and core-hole effects in background determination....... 6 6.6 Determining the background for inhomogeneous materials 6 7 Comparisons of procedures for removing effects of inelastic electron scattering from

Foreword

ISO (the International Organization for Standardization) is a worldwide federation of national standards bodies (ISO member bodies). The work of preparing International Standards is normally carried out through ISO technical committees. Each member body interested in a subject for which a technical committee has been established has the right to be represented on that committee. International organizations, governmental and non-governmental, in liaison with ISO, also take part in the work. ISO collaborates closely with the International Electrotechnical Commission (IEC) on all matters of electrotechnical standardization.

International Standards are drafted in accordance with the rules given in the ISO/IEC Directives, Part 2.

The main task of technical committees is to prepare International Standards. Draft International Standards adopted by the technical committees are circulated to the member bodies for voting. Publication as an International Standard requires approval by at least 75 % of the member bodies casting a vote.

In exceptional circumstances, when a technical committee has collected data of a different kind from that which is normally published as an International Standard ("state of the art", for example), it may decide by a simple majority vote of its participating members to publish a Technical Report. A Technical Report is entirely informative in nature and does not have to be reviewed until the data it provides are considered to be no longer valid or useful.

Attention is drawn to the possibility that some of the elements of this document may be the subject of patent rights. ISO shall not be held responsible for identifying any or all such patent rights.

ISO/TR 18392 was prepared by Technical Committee ISO/TC 201, *Surface chemical analysis*, Subcommittee SC 5. *Auger electron spectroscopy*.

Introduction

This Technical Report gives guidance for determining backgrounds in X-ray photoelectron spectra. The methods of background determination described in this report are applicable for quantitative evaluation of spectra of photoelectrons and Auger electrons excited by X-rays from solid surfaces and surface nanostructures.

The use of background determination in X-ray photoelectron spectroscopy (XPS) has developed from the need (i) for accurate quantitative information on chemical composition (including in-depth composition) of surface/interface layers and nanostructures, (ii) for unambiguous identification of chemical states of surface species and (iii) for extracting electronic-structure information from photoelectron spectra excited from solids. It is therefore necessary to separate the intrinsic part of a spectrum, which is associated with the photoionization or photoexcitation process by the X-radiation of interest in XPS or the Auger-electron decay process and which is needed for further analysis, from other parts of the spectrum (the background) appearing due to other processes. There are widely used procedures available for background subtraction in XPS that are reviewed in detail in References [1] to [4]. Here, the most common procedures and their use are summarized, including methods (i) commonly available in commercial software systems, (ii) available and used in more advanced laboratories and (iii) used in individual laboratories to develop understanding of the processes reflected in the XPS spectra.

Surface chemical analysis — X-ray photoelectron spectroscopy — Procedures for determining backgrounds

1 Scope

This Technical Report gives guidance for determining backgrounds in X-ray photoelectron spectra. The methods of background determination described in this report are applicable for evaluation of spectra of photoelectrons and Auger electrons excited by X-rays from solid surfaces.

2 Terms and definitions

For the purposes of this document, the terms and definitions given in ISO 18115 [5] apply.

3 Symbols and abbreviated terms

AES Auger electron spectroscopy

PIA Partial intensity analysis

QUASESTM Quantitative analysis of surfaces by electron spectroscopy

REELS Reflection electron energy loss spectroscopy

XPS X-ray photoelectron spectroscopy

4 Types of background in XPS

The electrons produced by X-ray irradiation of surfaces are either photoelectrons (as a result of the primary photoionization process) or Auger electrons (as a result of the secondary, core-hole decay process). Contributions to the measured spectra (i.e., electron energy distributions) from electrons scattered inelastically in the sample, from the secondary electron cascade, and — in the case of excitation by non-monochromatic X-ray irradiation — from photoelectrons induced by X-ray satellites and by bremsstrahlung radiation constitute the background. It is usually not necessary in practical XPS to determine the secondary-electron cascade background at low energies.

In this Technical Report, a description of methods for removing X-ray satellites is given in Clause 5 and for removing inelastic electron scattering in Clause 6. A brief comparison is given in Clause 7 of the effectiveness of procedures for removing the effects of electron inelastic scattering from electron spectra.

NOTE 1 In some cases, the intensity of the intrinsic part of a spectrum is distributed among features attributable to the "no-loss" main peak and to various electronic excitations associated with the creation of the core hole. The latter intrinsic contributions are sometimes denoted as the "intrinsic background". The identification of the intrinsic loss features and measurement of their intensities can be important for quantitative applications of XPS.

NOTE 2 Time-varying fluctuations of the analytical signal due to sources of noise [5] will lead to uncertainty in the signal intensity. Intensity contributions due to noise are not included in the types of background discussed in this Technical Report.

Removal of X-ray satellites from electron spectra

For XPS with non-monochromated X-ray sources, a fixed satellite structure is associated with the exciting main X-ray line (often Al or Mg K α radiation). These X-ray satellites lead to corresponding features in the XPS spectra.

For selected photoelectron peaks measured with Al or Mg X-ray sources, intensity is removed from higher-kinetic-energy channels corresponding to the energy differences between the $K\alpha_{3,4}$, $K\beta$, etc., X-ray satellite positions and the $K\alpha_{1,2}$ main peak and the corresponding intensity ratios [6] to remove the satellite contributions in the given spectral region. In such a way, scaled photoelectron peaks corresponding to the peaks excited by the X-ray satellites are subtracted. This subtraction process can be applied in turn to remove satellite peaks associated with other photoelectron peaks. The subtraction process may also erroneously remove an equivalent intensity from Auger peaks present in the spectrum if these are mistakenly identified as photoelectron peaks.

Estimation and removal of inelastic electron scattering from electron spectra

General Information

Various procedures have been developed for separating the part of intrinsic origin in the measured photo-excited electron spectra from the contributions due to electrons that are inelastically scattered in the sample [1-4]. These procedures (including those described in Clause 5) are usually applied to XPS data following data acquisition and require digital-data acquisition and handling capability.

Prior to application of a procedure for removing the inelastic electron scattering, a measured spectrum normally should be corrected for the spectrometer response function [7, 8] in cases where the distortion of the spectral shape due to instrumental effects is not negligible. To remove the effect of inelastic electron scattering in the spectrum, two different strategies can be followed: either to remove (subtract) the contribution attributable to electron inelastic scattering from the spectrum, or to include a background component in the model function being used to fit the spectrum. The electron-scattering contribution can be considered either as a background for the whole spectrum or as a sum of tail contributions [9, 10] from individual photoelectron peaks. In the case of background removal/subtraction, the parameters of the background components are fixed and, after creating such a background, can be subtracted from the measured spectrum. In the case of background fitting, some or all of the parameters of the background components are allowed to vary in the fitting process.

The methods described here for removing the contributions of electron inelastic scattering from a spectrum may not be used for some specific applications of XPS (i.e., total reflection XPS or Auger-photoelectron coincidence spectroscopy) without further consideration.

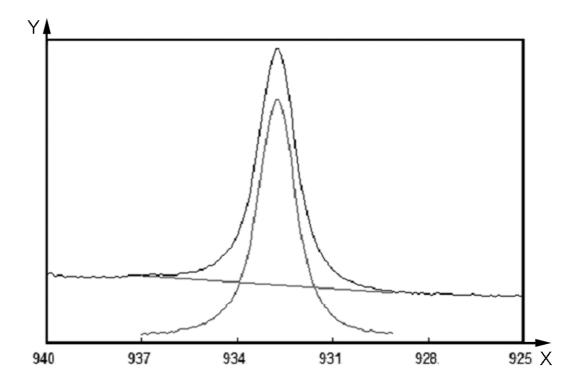
Procedures to account for inelastic electron scattering

6.2.1 Introduction

Even in the case of very thin samples, a considerable fraction of the electrons in a spectrum have been inelastically scattered; therefore, the estimation of the background for inelastic electron scattering is very important for quantitative applications. Common procedures for removing the effects of inelastic scattering are briefly described.

6.2.2 Estimation of the linear background and its removal

In this widely used method, two arbitrarily chosen points in the spectrum are selected and joined by a straight line [2] as an approximation of the true background. These points are generally chosen such that the peak is positioned between them. The intensity values at the chosen points may be the values at the corresponding energies or the average value over a small energy interval around the chosen points. Figure 1 illustrates a linear background for a Cu $2p_{3/2}$ XPS spectrum [11]. This is the most popular method for insulators, where the straight line is horizontal. This approach is used for polymers with great success for peak fitting. However, the use of the linear background in the case of peaks of transition metals (e.g., Fe 2p) leads to significant systematic errors in estimating the peak areas.



Key

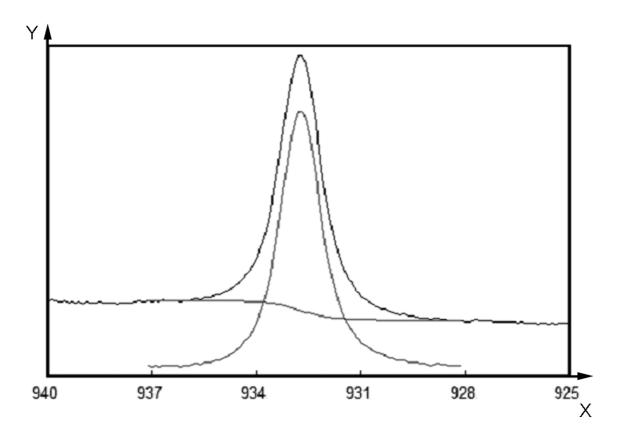
- X binding energy (eV)
- Y intensity (arbitrary units)

Figure 1 — Example of linear background and its subtraction

(The XPS spectrum used here is copper 2p_{3/2}. The upper curve shows the measured spectrum and the linear background. The lower curve is the spectrum after subtraction of the background.)

6.2.3 Integral background removal

This (widely used) method, proposed by Shirley [12, 13], employs a mathematical algorithm to approximate the inelastic scattering of electrons as they escape from the solid. The algorithm is based on the assumption that the background is proportional to the area of the peak above the background at higher kinetic energies. This method has been modified to optimize the required iterations [14], to provide for a sloping inelastic background [15], to provide for a background based upon the shape of the loss spectrum from an elastically backscattered electron [16], and to include a band gap for insulators [2]. Figure 2 shows the Shirley or integral background for the Cu $2p_{3/2}$ XPS spectrum given in Figure 1 [11] and the spectrum after this background has been subtracted. It should be emphasized that the correct use of this method requires the application of the valid algorithm [12] and the proper iteration limit [14].



Key

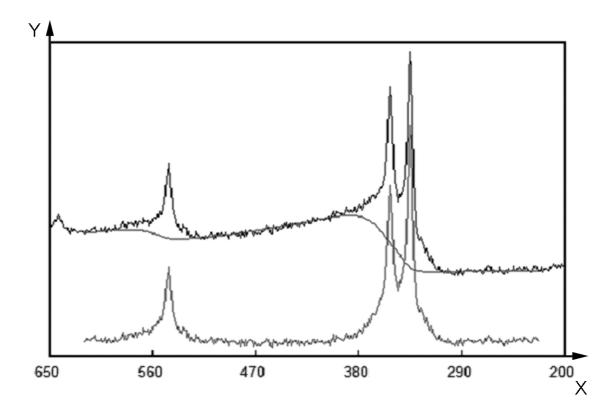
- X binding energy (eV)
- Y intensity (arbitrary units)

Figure 2 — Example of integral background and its subtraction

(The XPS spectrum used is copper $2p_{3/2}$. The upper curve shows the measured spectrum and the integral background. The lower curve is the spectrum after subtraction of the background.)

6.2.4 Removal based on the electron inelastic-scattering cross-section

This (often used) method, proposed by Tougaard ^[4], uses an algorithm that is based on a description of the inelastic-scattering processes taking place in the sample. The algorithm requires knowledge of the inelastic-scattering cross-section for the signal electrons in the sample material. This cross-section can be obtained from analysis of experimental reflected electron energy loss spectra ^[4, 17] or from a simple approximate formula, the so-called universal cross-section ^[4]. While the universal cross-section can be applied successfully in the case of many solids, more accurate simple formulas are available as well ^[18] for particular classes of material (e.g. polymers, Si, Al and other solids). Alternatively, the parameters used in the universal cross-section formula may be varied in an algorithm for estimating the inelastic background ^[19]. Figure 3 provides an example of the Tougaard background for Au 4p, 4d spectra and of these spectra after this background was subtracted ^[20].



Key

- X binding energy (eV)
- Y intensity (arbitrary units)

Figure 3 — Example of the Tougaard background and its subtraction

(The XPS spectrum used shows the gold 4p and 4d peaks. The upper curve shows the measured spectrum and the background obtained from use of the inelastic scattering cross-section. The lower curve is the spectrum after subtraction of the background.)

6.3 Procedures accounting for both inelastic and elastic scattering

It is the inelastic scattering of photoelectrons that produces the background. However, elastic scattering of the signal electrons affects their trajectories and therefore has an indirect effect on the background, which can be significant. For the case of homogeneous solids, this effect has been described analytically [21].

A useful method for modelling scattering effects in photo-induced electron spectra is to express the spectral shape in terms of the partial intensities of electrons that have participated in a given number of inelastic collisions ^[22]. This approach, known as partial intensity analysis (PIA), is based on the assumption that elastic deflections and energy losses of the scattered electrons are independent and can be considered separately. It is not necessary for the transmission function of the analyser to be known.

A further, although less frequently applied (because of its higher computational needs and limited practical use), method to account for scattering effects is the Monte Carlo simulation of the photo-induced electron spectra using various models and data sets for the material-dependent energy-loss functions, inelastic mean free paths, and differential cross-sections for elastic scattering [23].

6.4 Less commonly used procedures

Deconvoluting the photo-induced electron spectrum with the spectral shape of inelastically scattered electrons that typically have the same initial energy as the main peak in the photo-induced spectrum and its associated loss spectrum may also be used for background removal [24, 25] although an overcompensation of surface-loss

features is possible in this case. The intensity of the loss spectrum relative to that of the elastic peak is sometimes optimized, to allow for the angular dependence of the elastic-scattering cross-section in reflection electron energy loss spectroscopy (REELS) [26, 27]. Deconvolution is usually accomplished using Fourier transforms or iterative techniques [24, 25].

For removing the background formed by the low-energy secondary-electron cascade, the method proposed by Sickafus [28, 29] can be applied in which the logarithm of the measured spectral intensity is plotted as a function of the logarithm of the electron energy. Alternatively, a smoothing spline algorithm [30] can be used to obtain a structureless background between two chosen spectral regions, and this background can then be subtracted from the measured spectrum at intermediate energies.

6.5 Role of surface and core-hole effects in background determination

Surface excitations can significantly influence the shape of an energy loss spectrum and, as a consequence, the background. Methods for background determination that make use of inelastic-scattering cross-sections derived from experimental REELS spectra account for surface effects to some extent; it should be noted, however, that the magnitude of these effects strongly depends on the electron emission angle at the sample surface and the electron energy. The effect of surface excitations can essentially be accounted for even in the case of use of the universal inelastic-scattering cross-section by varying an appropriate parameter in the formula in a well-defined way [31]. Influence of surface roughness can also be significant, especially in the case of analysis at a near-grazing emission angle and of analysis with standards having a surface roughness different from that of the sample analysed.

The core hole created in the photoionization process can lead to the appearance of loss structures in the spectra induced by intrinsic excitation, and these loss structures can depend on the chemical environment of the ionized atom. While the methods for background subtraction that are based on the application of the inelastic electron-scattering cross-section model remove only the extrinsic part of the background, a Shirley-type background removes most contributions of both intrinsic and extrinsic origin. The contribution from intrinsic processes can be estimated by using the shape parameter (obtained by extrapolating the background to the peak centre to obtain a "background height" normalized by dividing by the peak area) as suggested by Castle and Salvi [32, 33]. The shape parameter is expected to be characteristic of a given element or its particular chemical form [32, 33].

Determining the background for inhomogeneous materials 6.6

For the case of inhomogeneous materials, it has been shown [4] that appreciably differing atomic concentration distributions (i.e. in-depth profiles) can result in identical photo-induced peak intensities for a particular XPS experimental configuration. Formulae to determine the inelastic background for inhomogeneous systems have been developed by Tougaard [34-36]. He showed that analysis of the inelastic spectral shape accompanying the photoelectron or Auger-electron peak for an element can yield the concentration distribution of that element in the sample, i.e. the in-depth concentration profile and the surface morphology on the nanometre scale [22, 37-45]. A non-destructive procedure for quantitative characterization of surface nanostructures is based on a formalism using an adjustable function describing the in-depth atomic concentration profile and the Tougaard universal inelastic-scattering cross-section; use may also be made of the reference spectrum for a standard sample with a known concentration profile such as a single elemental solid. The procedure is applicable either for obtaining the intrinsic atomic excitation spectrum (background removal) by adjusting the profile function or for determining the compositional profile (using a known atomic spectrum from analysis of a reference spectrum). The accuracy of the technique and other details are available in a review [4], and a software package known as QUASESTM (Quantitative Analysis of Surfaces by Electron Spectroscopy) [4] is available for spectrum analysis. Recent studies of the growth and in-depth compositional distribution of thin metal films on silicon from analyses of the inelastic spectral shape accompanying XPS lines have demonstrated the utility of this software [43, 44].

The PIA approach [22, 45] described in 6.3 can also be used to determine backgrounds in photo-induced electron spectra of inhomogeneous materials. In this formalism, a function that depends on the partial intensities of normalized energy distributions after a specified number of inelastic collisions is minimized. An XPS peak for the selected species is often measured at different emission angles when applying this procedure.

7 Comparisons of procedures for removing effects of inelastic electron scattering from electron spectra

Comparisons have been published of the most popular procedures for background removal [14, 15, 46-59]. The effect of the choice of the energy end points/regions on determinations of the peak area has been discussed for the cases of the linear background (6.2.2) and the integral background (6.2.3) [14, 15]. Further comparisons of these procedures and of the Tougaard procedure (6.2.4), including tests of their validity, have been published [46-59]. The general behaviour of Tougaard-style backgrounds in XPS, including effects of different cross-sections for inelastic scattering, has been analysed [27, 60]. A comprehensive review of electron transport in solids relevant to AES and XPS and of the influence of this electron transport on quantitative surface analysis has been published [61]. This review contains a detailed discussion and comparison of different methods for removing inelastic backgrounds and other spectral contributions from electron spectra.

Table 1 shows root-mean-square scatter factors for the ratios of measured XPS intensities for some 60 elemental solids to the corresponding calculated intensities with respect to the average value of this ratio for excitation by Al and Mg K α X-rays and for inelastic backgrounds determined from the Tougaard universal cross-section and from angle-averaged REELS cross-sections [27]. This analysis shows that the scatter factors are smaller (i.e. there is closer agreement between measured and calculated XPS intensities) if inelastic backgrounds are determined from REELS cross-sections instead of the Tougaard universal cross-section. The REELS cross-sections used in the analysis have not yet been published.

Table 1 — Root-mean-square scatter factors for the ratios of measured XPS intensities for some 60 elemental solids to the corresponding calculated intensities with respect to the average value of this ratio for excitation by Al and Mg K α X-rays and for inelastic backgrounds determined from the Tougaard universal cross-section and from angle-averaged REELS cross-sections [60]

Cross-section for inelastic scattering used to determine backgrounds	Exciting X-rays	
	ΑΙ Κα	Mg Kα
Universal	1,20	1,20
REELS (angle-averaged)	1,11	1,12

Bibliography

- [1] ASTM E 995-97, Standard Guide for Background Subtraction Techniques in Auger Electron and X-ray Photoelectron Spectroscopy
- BRIGGS, D. and SEAH, M.P. Practical Surface Analysis, Vol. 1, 1990, Wiley and Sons, New York, NY, [2] pp. 233-239 and pp. 555-586
- [3] GRANT, J.T. Background Subtraction Techniques in Surface Analysis, Journal of Vacuum Science and Technology A, April 1984, 2, No. 2, pp. 1135-1140
- [4] TOUGAARD, S. Accuracy of the Non-destructive Surface Nanostructure Quantification Technique Based on Analysis of the XPS or AES Peak Shape, Surface and Interface Analysis, April 1998, 26, No. 4, pp. 149-269
- [5] ISO 18115, Surface chemical analysis — Vocabulary
- [6] KLAUBER, C. Refinement of Magnesium and Aluminium Ka X-ray Source Functions, Surface and Interface Analysis, July 1993, 20, No. 8, pp. 703-715
- [7] SEAH, M.P. A system for the intensity calibration of electron spectrometers, J. Electron Spectroscopy and Related Phenomena, April 1995, 71, No. 3, pp. 191-204
- X-Ray Photoelectron Spectrometer Intensity Calibration Software, Version X1, National Physical [8] Laboratory, Teddington, Middlesex, United Kingdom, http://www.npl.co.uk/nanoanalysis/x1.html
- VÉGH, J. XPS Peak Shapes Accounting for the Inelastic Scattering of Photoelectrons, Surface and [9] Interface Analysis, July 1992, 18, No. 7, pp. 545-550
- VÉGH, J. Sloping Shirley-type Inelastic Line Shapes, Surface and Interface Analysis, September 1993, [10] **20**, No. 10, pp. 860-862
- YOSHITAKE, M. File 00001182, COMPRO, Common Data Processing System, Version 8, Surface [11] Analysis Society of Japan, http://www.sasj.jp/COMPRO/index.html
- SHIRLEY, D.A. High-Resolution X-ray Photoemission Spectrum of the Valence Bands of Au, Physical [12] Review B, 15 June 1972, 5, No. 12, pp. 4709-4714
- SEAH, M.P. and BROWN, M.T. Validation and Accuracy of Software for Peak Synthesis in XPS, Journal [13] of Electron Spectroscopy and Related Phenomena, Aug 1998, 95, No. 1, pp. 71-93
- [14] PROCTOR, A. and SHERWOOD, P.M.A. Data Analysis Techniques in X-ray Photoelectron Spectroscopy, Analytical Chemistry, 1982, 54, No. 1, pp. 13-19
- BISHOP, H.E. Practical Peak Area Measurements in X-ray Photoelectron Spectroscopy, Surface and [15] Interface Analysis, December 1981, 3, No. 6, pp. 272-274
- BURRELL, M.C. and ARMSTRONG, N.R. A Sequential Method for Removing the Inelastic Loss [16] Contribution from Auger Electron Spectroscopic Data, Applications of Surface Science, Sept-Oct 1983, 17, No. 1, pp. 53-69
- [17] TOUGAARD, S. and KRAAER, J. Inelastic-electron-scattering cross-sections for Si, Cu, Ag, Au, Ti, Fe and Pd, *Physical Review* B, 15 January 1991, **43**, No. 2, pp. 1651-1661
- [18] TOUGAARD, S. Universality Classes of Inelastic Electron Scattering Cross-sections, Surface and Interface Analysis, March 1997, 25, No. 3, pp. 137-154

- [19] TOUGAARD, S. Practical Algorithm for Background Subtraction, *Surface Science*, 2 June 1989, **216**, No. 3, pp. 343-360
- [20] YOSHITAKE, M. File 0000179, COMPRO, Common Data Processing System, Version 8, Surface Analysis Society of Japan, http://www.sasj.jp/COMPRO/index.html
- [21] TILININ, I.S., JABLONSKI, A. and TOUGAARD, S. Path-length distribution of photoelectrons emitted from homogeneous noncrystalline solids Consequences for inelastic-background analysis, *Physical Review B*, 15 August 1995, **52**, No. 8, pp. 5935-5946
- [22] WERNER, W.S.M. Partial Intensity Analysis (PIA) for Quantitative Electron Spectroscopy, *Surface and Interface Analysis*, October 1995, **23**, No. 11, pp. 737-752
- [23] NAGATOMI, T., DING, Z.-J. and SHIMIZU, R. Derivation of New Energy Loss Functions as Applied to Analysis of Si 2p XPS Spectra, *Surface Science*, July 1996, **359**, No. 1-3, pp. 163-173
- [24] CARLEY, A.F. and JOYNER, R.W. The Application of Deconvolution Methods in Electron Spectroscopy A Review, *Journal of Electron Spectroscopy and Related Phenomena*, 1979, **16**, No. 1, pp. 1-23
- [25] KOENIG, M.F. and GRANT, J.T. Deconvolution in X-ray Photoelectron Spectroscopy, *Journal of Electron Spectroscopy and Related Phenomena*, 1984, **33**, No. 1, pp. 9-22
- [26] SEAH, M.P. Background Subtraction Part III: The application of REELS data to background removal in AES and XPS, *Surface Science*, 10 January 2001, **471**, No. 1-3, pp. 185-202
- [27] SEAH, M.P., GILMORE, I.S. and SPENCER, S.J. Quantitative AES IX and quantitative XPS II Auger and X-ray photoelectron intensities and sensitivity factors from spectral digital databases reanalysed using a REELS database, *Surface and Interface Analysis*, August 2001, **31**, No. 8, pp. 778-795
- [28] SICKAFUS, E.N. Linearized Secondary-Electron Cascades for the Surfaces of Metals Part I: Clean Surfaces of Homogeneous Metals, *Physical Review B*, 15 August 1977, **16**, No. 4, pp. 1436-1447
- [29] SICKAFUS, E.N. Linearized Secondary-Electron Cascades for the Surfaces of Metals Part II: Surface and Subsurface Sources, *Physical Review B*, 15 August 1977, **16**, No. 4, pp. 1448-1458
- [30] HESSE, R., LITTMARK, U. and STAIB, P. A Method for Background Determination in Quantitative Auger Spectroscopy, *Applied Physics*, November 1976, **11**, No. 3, pp. 233-239
- [31] SIMONSEN, A. and TOUGAARD, S. Analysis of angle-resolved electron energy loss in XPS spectra of Ag, Au, Co, Cu, Fe and Si, *Surface Science*, 10 August 1999, **436**, No. 1-3, pp. 149-159
- [32] SALVI, A.M. and CASTLE, J.E. The intrinsic asymmetry component of the 'total background' in XP spectra, *Journal of Electron Spectroscopy and Related Phenomena*, June 1998, **94**, No. 1-2, pp. 73-87
- [33] CASTLE, J.E. and SALVI, A.M. Chemical state information from the near-peak region of the X-ray photoelectron background, *Journal of Electron Spectroscopy and Related Phenomena*, March 2001, **114-116**, pp. 1103-1113
- [34] TOUGAARD, S. Deconvolution of Loss Features from Electron Spectra, *Surface Science*, 1 April 1984, **139**, No. 1, pp. 208-218
- [35] TOUGAARD, S. Practical Algorithm for Background Subtraction, *Surface Science*, 2 June 1989, **216**, No. 3, pp. 343-360
- [36] TOUGAARD, S. Inelastic Background Removal in XPS from Homogeneous and Inhomogeneous Solids, Journal of Vacuum Science and Technology A, July 1987, 5, No. 4, pp. 1230-1234

- [37] TOUGAARD, S. In-Depth Concentration Profile Information through Analysis of the Entire XPS Peak Shape, Applied Surface Science, July 1988, 32, No. 3, pp. 332-337
- [38] TOUGAARD, S. Inelastic Background Correction and Quantitative Surface Analysis, Journal of Electron Spectroscopy and Related Phenomena, 1990, 52, pp. 243-271
- TOUGAARD, S. and HANSEN, H.S., Non-Destructive Depth Profiling through Quantitative Analysis of [39] Surface Electron Spectra, Surface and Interface Analysis, November 1989, 14, No. 11, pp. 730-738
- HANSEN, H.S., JANSSON, C. and TOUGAARD, S. Inelastic Peak Shape Method Applied to Quantitative [40] Surface Analysis of Inhomogeneous Samples, Journal of Vacuum Science and Technology A, July 1992, **10**, No. 4, pp. 2938-2944
- TOUGAARD, S. Quantitative XPS Non-destructive Analysis of Surface Nano-Structures, Applied [41] Surface Science, 2 July 1996, **100-101**, pp. 1-10
- [42] TOUGAARD, S. Surface Nanostructure Determination by X-ray Photoemission Spectroscopy peak Shape Analysis, Journal of Vacuum Science and Technology A, May 1996, 14, No. 3, pp. 1415-1423
- [43] SCHLEPBERGER, M., FUJITA, D., SCHARFSCHWERDT, C. and TOUGAARD, S. Growth and In-depth Distribution of Thin Metal Films on Silicon (111) Studied by XPS — Inelastic Peak Shape analysis, Surface Science, 1 July 1995, 331-333, Part 2, pp. 942-947
- [44] SCHLEPBERGER, M., FUJITA, D., SCHARFSCHWERDT, C., TOUGAARD, S. Nanostructure of Thin Metal Films on Silicon (111) Investigated by X-ray Photoelectron Spectroscopy — Inelastic Peak Shape Analysis, Journal of Vacuum Science and Technology B, May 1995, 13, No. 3, 949-953
- WERNER, W.S.M. Slowing down of medium-energy electrons in solids, *Physical Review B*, 1 June 1997, [45] **55**, No. 22, pp. 14925-14934
- TOUGAARD, S. and JANSSON, C. Background Correction in XPS Comparison of Validity of Different [46] Methods, Surface and Interface Analysis, June 1992, 19, No. 1-12, pp. 171-174
- TOKUTAKA, H., ISHIHARA, N., NISHIMORI, K., KISHIDA, S. and ISOMOTO, K. Background Removal in X-ray [47] Photoelectron Spectroscopy, Surface and Interface Analysis, October 1992, 18, No. 10, pp. 697-704
- TOUGAARD, S., BRAUN, W., HOLUB-KRAPPE, E. and SAALFELD, H. Test of Algorithm for Background [48] Correction in XPS Under Variation of XPS Peak Energy, Surface and Interface Analysis, December 1998, **13**, No. 4, pp. 225-227
- REPOUX, M. Comparison of Background Removal Methods for XPS, Surface and Interface Analysis, [49] August 1992, 18, No. 5, pp. 567-670
- JANSSON, C., HANSEN, H.S., JUNG, C., BRAUN, W. and TOUGAARD, S. Validity of Background Correction [50] Algorithms Studied by Comparison with Theory of Synchrotron-radiation-excited Core Levels and Their Corresponding Auger Peak Intensities, Surface and Interface Analysis, June 1992, 19, No. 1-12, pp. 217-221
- HANSEN, H.S., JANSSON, C. and TOUGAARD, S. Inelastic Peak Shape Method Applied to Quantitative [51] Surface Analysis of Inhomogeneous Samples, Journal of Vacuum Science and Technology A, July 1992, **10**, No. 5, pp. 2938-2944
- TOUGAARD, S. and JANSSON, C. Comparison of Validity and Consistency of Methods for Quantitative [52] XPS Peaks Analysis, Surface and Interface Analysis, December 1993, 20, No. 13, pp. 1013-1046
- JANSSON, C., TOUGAARD, S., BEAMSON, G., BRIGGS, D., DENCH, S.F., ROSSIE, A., HAVERT, R., HUBI, G., [53] Brown, N.M.D., Meenan, B.J., Anderson, C.A., Repoux, M., Malitesta, C. and Sabbatini, L. Intercomparison of Algorithms for Background Correction in XPS, Surface and Interface Analysis, July 1995, 23, No. 7-8, pp. 484-494

- [54] JANSSON, C., HANSEN, H.S., YUBERO, F. and TOUGAARD, S. Accuracy of the Tougaard Method for Quantitative Surface Analysis. Comparison of the Universal and REELS Inelastic Cross-Sections, *Journal of Electron Spectroscopy and Related Phenomena*, 18 December 1992, **60**, No. 4, pp. 301-319
- [55] YUBERO, F., JANSSON, C., BATCHELOR, D.R., TOUGAARD, S. Validity of the Method for Quantitative XPS of Surface Nano-structures Application to Cu/Au/Cu, *Surface Science*, 1 July 1995, **331-333**, Part 1, pp. 753-758
- [56] TOUGAARD, S. Accuracy of the Non-destructive Surface Nanostructure Quantification Technique Based on Analysis of the XPS or AES Peak Shape, *Surface and Interface Analysis*, April 1998, **26**, No. 4, pp. 249-269
- [57] SIMONSEN, A.C., SCHLEBERGER, M., TOUGAARD, S., HANSEN, J.L. and NYLANDSTED, L.A. Nanostructure of Ge deposited on Si(001) A Study by XPS Peak Shape Analysis and AFM, *Thin Solid Films*, 11 January 1999, **338**, No. 1-2, 165-171
- [58] SIMONSEN, A.C., POHLER, J.P., JEYNES, C. and TOUGAARD, S. Quantification of Au deposited on Ni XPS Peak Shape Analysis Compared to RBS, *Surface and Interface Analysis*, January 1999, **27**, No. 1, pp. 52-56
- [59] SEAH, M.P. Background subtraction Part I: General behaviour of Tougaard-style backgrounds in AES and XPS, *Surface Science*, January 1999, **420**, No. 2-3, pp. 285-294
- [60] SEAH, M.P., GILMORE, I.S. and SPENCER, S.J. Background subtraction Part II: General behaviour of REELS and universal cross-section in the removal of backgrounds in AES and XPS, *Surface Science*, August 2000, **461**, No. 1-3, pp. 1-15
- [61] WERNER, W.S.M. Electron transport in solids for quantitative surface analysis, *Surface and Interface Analysis*, March 2001, **31**, No. 3, pp. 141-176

No reproduction or networking permitted without license from IHS



ICS 71.040.40

Price based on 11 pages